

ABSTRACT OF THE DISCLOSURE

A laser apparatus includes a semiconductor laser element having a first active layer made of a GaN-based compound, and emitting first laser light; and a surface-emitting semiconductor element having a second active layer made of a GaN-based compound, being excited with the first laser light, and emitting second laser light. In addition, the surface-emitting semiconductor element may have a first mirror arranged on one side of the second active layer, and a second mirror may be arranged outside the surface-emitting semiconductor element so that the first and second mirrors form a resonator.

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